

ABSTRACT OF THE DISCLOSURE

A nitride semiconductor laser device includes a nitride semiconductor substrate, and a layered portion corresponding to a nitride semiconductor film grown on the nitride semiconductor substrate, the
5 layered portion including an n-type layer and a p-type layer and a light emitting layer posed between the n- and p-type layers, of the n- and p-type layers a layer opposite to the nitride semiconductor substrate with the light emitting layer opposed therebetween serving as an upper layer having a stripe of 1.9 μm to 3.0 μm in width, the light emitting layer and the upper
10 layer having an interface distant from a bottom of the stripe by 0 μm to 0.2 μm .